

CIR-S3SUSOM1602G 256M words X 64 bits, 1 rank,) \$&

DDR3 SO-DIMM 1600MHz 2GB

Description

The CIR-S3SUSOM1602G is 256M words X 64 bits, 1 rank. Unbuffered Small Outline Dual In-Line Memory Module (SO-DIMM). DDR3 SDRAMs in Fine Ball Grid Array (FBGA) packages on a 204pin glass-epoxy substrate. Provide a high performance 8 byte interface in 67.60mm width form factor of industry standard. It is suitable for easy interchange and addition.

Specifications

Density	2GB
Pin Count	204pin
Type	Unbuffered
Dimensions	67.6mm x 30.0mm
ECC	Non-ECC
Component Config	256M x 8 bit
Data Rate	1600 MHz
CAS Latency	11
Voltage	1.5V / 1.35V
PCB Layers	8
Operating Temp.	0°C~+85°C
Module Ranks	Single Rank

Features

- Data rate: 1600MHz
- RoHS compliant products.
- 204pin, Small outline single in-line memory module (SO-DIMM)
- VDDQ= 1.35V (1.28V~1.45V) & VDDQ=1.5V(1.425V~1.575V)
- Programmable CAS Latency (CL): 6, 7, 8, 9, 10, 11 support
- Fully differential clock inputs (CK, /CK) operation
- Differential Data Strobe (DQS, /DQS)
- Serial presence detect with EEPROM
- 8 independent internal bank
- 8K refresh cycles / 64ms
- On Die Termination supported
- Asynchronous RESET pin supported
- ZQ calibration supported
- Programmable Additive Latency (Posted CAS) : 0, CL - 2, or CL - 1 clock
- Bi-directional Differential Data Strobe
- Burst Length: 4, 8
- 8 bit pre-fetch
- Average Refresh Period 7.8us at $0^{\circ}\text{C} \leq \text{TC} \leq 85^{\circ}\text{C}$
3.9us at $85^{\circ}\text{C} < \text{TC} \leq 95^{\circ}\text{C}$

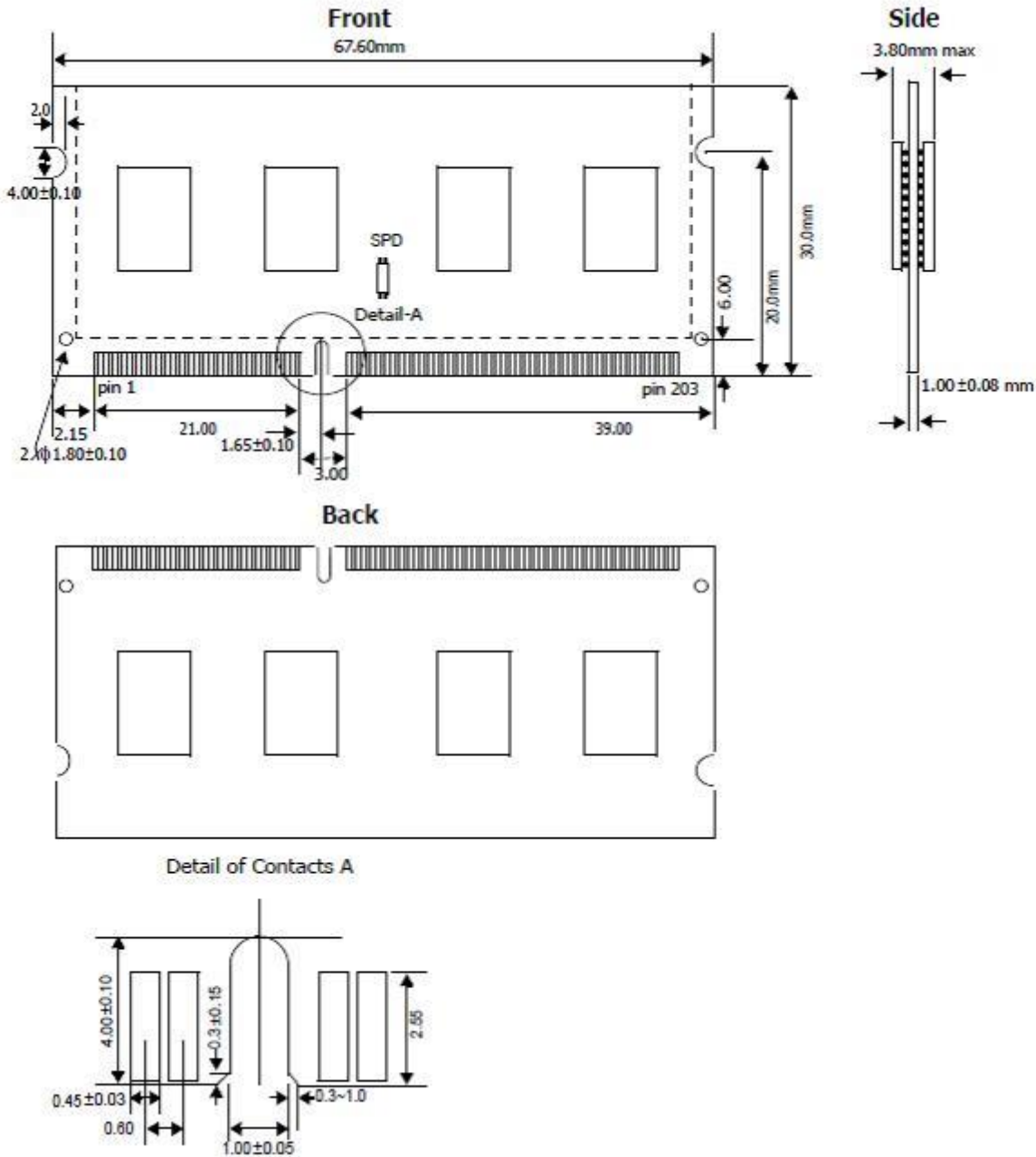


Speed Grade

Frequency Grade	Data Transfer Rate	CAS Latency Support						CL-tRCD-tRP
		CL6	CL7	CL8	CL9	CL10	CL11	
DDR3-1600	PC3-12800	800	1066	1066	1333	1333	1600	11-11-11

Package Dimensions

Unit: mm



Tolerances : ± 0.15mm unless otherwise specified